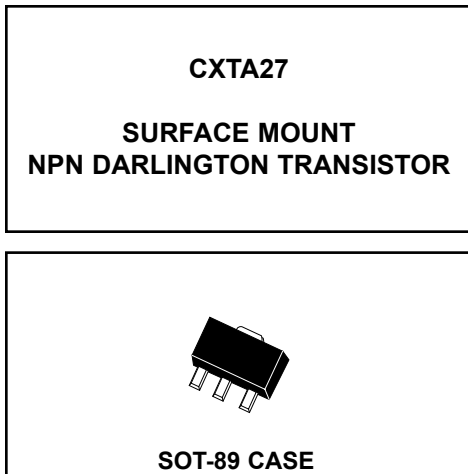




CentralTM

Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CXTA27 type is a NPN Silicon Darlington Transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for applications requiring extremely high gain.

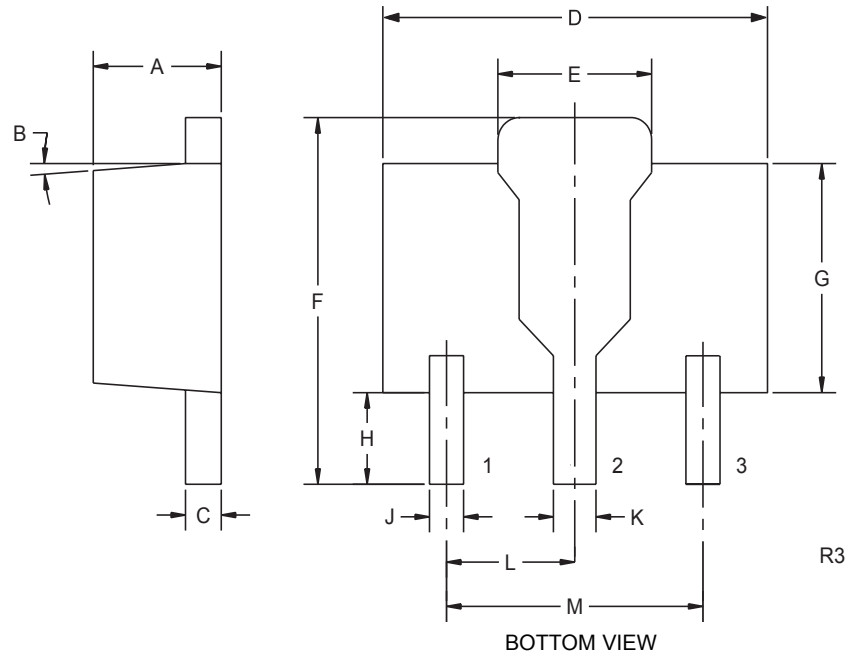
MAXIMUM RATINGS (T _A =25°C)			
	SYMBOL		UNITS
Collector-Emitter Voltage	V _{CES}	60	V
Emitter-Base Voltage	V _{EBO}	10	V
Collector Current	I _C	500	mA
Power Dissipation	P _D	1.2	W
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	Θ _{JA}	104	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{CBO}	V _{CB} =50V		100	nA
I _{CES}	V _{CE} =50V		500	nA
I _{EBO}	V _{EB} =10V		100	nA
BV _{CBO}	I _C =100μA	60		V
BV _{CES}	I _C =100μA	60		V
V _{CE(SAT)}	I _C =100mA, I _B =0.1mA		1.5	V
V _{BE(ON)}	V _{CE} =5.0V, I _C =100mA		2.0	V
h _{FE}	V _{CE} =5.0V, I _C =10mA	10,000		
h _{FE}	V _{CE} =5.0V, I _C =100mA	10,000		
f _T	V _{CE} =50V, I _C =10mA, f=100MHz	125		MHz

**SURFACE MOUNT
NPN DARLINGTON TRANSISTOR**

SOT-89 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) EMITTER
- 2) COLLECTOR
- 3) BASE

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.055	0.067	1.40	1.70
B	4°		4°	
C	0.016	0.018	0.40	0.46
D	0.173	0.185	4.40	4.70
E	0.070	0.074	1.79	1.87
F	0.146	0.177	3.70	4.50
G	0.094	0.106	2.40	2.70
H	0.028	0.051	0.70	1.30
J	0.015	0.019	0.38	0.48
K	0.019	0.023	0.48	0.58
L	0.059		1.50	
M	0.118		3.00	

SOT-89 (REV: R3)

R1 (19-December 2001)